WEST Search History

Hide Items 1 Restore Clear Cancel

DATE: Thursday, September 20, 2007

Hide?	Set Name	Query	Hit Count
	DB = USPT;	PLUR=YES; OP=ADJ	
	L8	L2 and 510/\$.ccls.	24
	L7	L2 and 134/\$.ccls.	19
	L6	(5545353 or 5556482 or 4904571).pn.	3
	DB=PGPB,	USPT, USOC, EPAB, JPAB, DWPI, TDBD; P	LUR=YES; OP=ADJ
Ņ	L5	L2 and carbamate	1
	L4	L2 with carbamate	0
Γī	L3	L2 with carbonate	2
	L2	L1 with amines	151
	L1	photoresist with removing	27902

END OF SEARCH HISTORY

Hit List

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Search Results - Record(s) 1 through 10 of 19 returned.

☐ 1. Document ID: US 7056872 B2

L7: Entry 1 of 19

File: USPT

Jun 6, 2006

US-PAT-NO: 7056872

DOCUMENT-IDENTIFIER: US 7056872 B2

TITLE: Solution composition for removing a remaining photoresist resin

DATE-ISSUED: June 6, 2006

PRIOR-PUBLICATION: `

DOC-ID

DATE

US 20030060382 A1

March 27, 2003

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY Lee; Geun Su Kyoungki-do KR KR Chung; Jae Chang Kyoungki-Do KR Shin; Ki Soo Kyoungki-do Oh: Kee Joon Kyoungki-do KR

US-CL-CURRENT: 510/175; 134/2, 134/3, 438/692, 510/176, 510/254, 510/255, 510/499

ABSTRACT:

Cleaning solutions for removing photoresist resins remaining on the underlying layer patterns formed by photolithography process using the photoresist patterns as etching mask. The cleaning solution for removing photoresist comprises H.sub.20 as solvent, amine compounds, hydrazine hydrate, transition metal-removing material and alkali metal-removing material. Photoresist coated on the top portion of underlying layers can be rapidly and effectively removed by the disclosed cleaning solution. In addition, the cleaning solution is environment-friendly because H.sub.20 is used as the solvent, and has little effect on metal layers when underlying layers are formed of metals.

10 Claims, 5 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 3

Full Title Citation Front Review Classification Date Reference	Claims	ns KWWC Dr
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Record List Display Page 2 of 9

☐ 2. Document ID: US 7049275 B2

L7: Entry 2 of 19 File: USPT May 23, 2006

US-PAT-NO: 7049275

DOCUMENT-IDENTIFIER: US 7049275 B2

TITLE: Photoresist stripping composition and cleaning composition

DATE-ISSUED: May 23, 2006

PRIOR-PUBLICATION:

DOC-ID DATE

US 20030181344 A1 September 25, 2003

INVENTOR-INFORMATION:

NAME CITY ZIP CODE COUNTRY STATE Ikemoto; Kazuto Tokyo . JΡ Yamamoto; Yoshiaki JΡ Niigata Yoshida; Hiroshi JΡ Chiba Maruyama; Taketo Chiba JP

US-CL-CURRENT: 510/176; 134/1.3, 134/2, 510/175, 510/245, 510/255, 510/499

ABSTRACT:

The photoresist stripping composition of the present invention contains at least one oxymethylamine compound represented by the following formula 1: ##STR00001## wherein R.sup.1 to R.sup.3 are as defined in the specification. Of the oxymethylamine compound of the formula 1, the compound represented by the following formula 7: ##STR00002## wherein R.sup.2 to R.sup.5 and n are as defined in the specification, is a novel compound.

35 Claims, 2 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 2

Full	Title	Citation	Front	Review	Classification	Date	Reference	10 Am 1 2 2 10	1	Claims	KOMC	Draw, De
-												

☐ 3. Document ID: US 7037852 B2

L7: Entry 3 of 19

File: USPT

May 2, 2006

US-PAT-NO: 7037852

DOCUMENT-IDENTIFIER: US 7037852 B2

TITLE: Composition for stripping photoresist and method of preparing the same

DATE-ISSUED: May 2, 2006

PRIOR-PUBLICATION:

Record List Display Page 3 of 9

DOC-ID

DATE

US 20040063595 A1

April 1, 2004

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY Park; Dong-jin Osan-si KR[°] Kim; Jin-sung Suwon-si KR Jun; Pil-kwon Yongin-si KR Hwang; Jin-ho KR Suwon-si Sohn; Il-hyun Suwon-si KR

US-CL-CURRENT: 438/745; 134/1.2, 134/1.3, 252/79.1, 252/79.4, 257/E21.255, 438/749

ABSTRACT:

A composition for stripping photoresist, methods of preparing and forming the same, a method of manufacturing a semiconductor device using the composition, and a method of removing a photoresist pattern from an underlying layer using the composition, where the composition may include an ethoxy N-hydroxyalkyl alkanamide represented by the formula, CH.sub.3CH.sub.2--O--R.sub.3--CO-N--R.sub.1R.sub.2OH, an alkanolamine and a polar material. Raw materials of alkyl alkoxy alkanoate, represented by a chemical formula of R.sub.4--O--R.sub.3--COOR.sub.5, and alkanolamine, represented by a chemical formula of NHR.sub.1R.sub.2OH, may be mixed to form a mixture, which is stirred and cooled to obtain the composition. The composition may balance exfoliation and dissolution of photoresist patterns, and may potentially eliminate thread-type residues from remaining on a surface of an underlying layer after removing the photoresist patterns.

26 Claims, 8 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 5

Full Title C	itation Fro	nt Review	Classification	Date Reference		Claims	KOMC	Draw, D
	ocument I	D. 11S 68	275709 B2		•			

US-PAT-NO: 6875709

DOCUMENT-IDENTIFIER: US 6875709 B2

TITLE: Application of a supercritical CO2 system for curing low k dielectric

materials

DATE-ISSUED: April 5, 2005

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY
Lin; Chun-Hsien Hsin Chu TW
Lo; Henry Hsinchu TW
Liu; Anthony Hsinchu TW

Record List Display

Lin; Yu-Liang

Hsin-Chu

TW

US-CL-CURRENT: <u>438/781</u>; <u>134/10</u>, <u>134/12</u>, <u>257/E21.242</u>, <u>257/E21.259</u>, <u>257/E21.262</u>, <u>257/E21.576</u>, <u>438/782</u>, 438/793

ABSTRACT:

A method and apparatus for curing and modifying a low k dielectric layer in an interconnect structure is disclosed. A spin-on low k dielectric layer which includes an organic silsesquioxane, polyarylether, bisbenzocyclobuene, or SiLK is spin coated on a substrate. The substrate is placed in a process chamber in a supercritical CO.sub.2 system and is treated at a temperature between 30.degree. C. and 150.degree. C. and at a pressure from 70 to 700 atmospheres. A co-solvent such as CF.sub.3 --X or F--X is added that selectively replaces C--CH.sub.3 bonds with C--CF.sub.3 or C--F bonds. Alternatively, H.sub.2 O.sub.2 is employed as co-solvent to replace a halogen in a C--Z bond where Z=F, Cl, or Br with an hydroxyl group. Two co-solvents may be combined with CO.sub.2 for more flexibility. The cured dielectric layer has improved properties that include better adhesion, lower k value, increased hardness, and a higher elastic modulus.

78 Claims, 6 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 3

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Pitachnel (\$	Claims	KWC	Draw, De

5. Document ID: US 6841526 B2

L7: Entry 5 of 19

File: USPT

Jan 11, 2005

US-PAT-NO: 6841526

DOCUMENT-IDENTIFIER: US 6841526 B2

** See image for Certificate of Correction **

TITLE: Cleaning solution for removing photoresist

DATE-ISSUED: January 11, 2005

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY
Lee; Geun Su Kyoungki-do KR
Jung; Jae Chang Kyoungki-do KR
Shin; Ki Soo Seoul KR

US-CL-CURRENT: 510/176; 134/2, 134/42, 430/331, 510/175, 510/255

ABSTRACT:

Cleaning solutions for removing photoresist materials and a method of forming underlying layer patterns of semiconductor devices using the same. The cleaning solutions for removing photoresist include a solvent mixture of H.sub.2 O and an organic solvent, an <u>amine</u> compound, a transition metal<u>-removing</u> material and an alkali metal-removing material, and may further include a hydrazine hydrate.

Record List Display Page 5 of 9

17 Claims, 7 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 7

Full Title Citation Front Review Classification Date Reference Claims KWC Draw. Do

☐ 6. Document ID: US 6652666 B2

L7: Entry 6 of 19

File: USPT

Nov 25, 2003

US-PAT-NO: 6652666

DOCUMENT-IDENTIFIER: US 6652666 B2

TITLE: Wet dip method for photoresist and polymer stripping without buffer

treatment step

DATE-ISSUED: November 25, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP COD	E C	COUNTRY
Ma; Ching-Tien	Kaohsiung			מ	TW
Shih; Chen-Hsi	Yung Kang			מ	ΓW
Chen; Dian-Hau	Hsin-Chu			7	rw
Lu; Gau-Ming	Taipei			7	rw
Chen; Cho-Ching	Tainan			ר	ΓW

US-CL-CURRENT: <u>134/30</u>; <u>134/19</u>, <u>134/38</u>, <u>134/902</u>, <u>257/E21.228</u>, <u>257/E21.255</u>

ABSTRACT:

A wet dip method for photoresist and polymer stripping from a wafer surface without the need for a buffer solvent treatment step is disclosed. In the method, the wafer is first exposed to an etchant solution that is maintained at a temperature of at least 80.degree. C. The wafer is then cooled in a room temperature air for a sufficient length of time until the temperature of the wafer reaches substantially room temperature. The wafer is then rinsed in a rinsing step that includes a quick dump rinse and a final rinse with deionized water that is maintained at a temperature not higher than room temperature without first exposing the wafer to a buffer solvent such as that required in a conventional wet dip method.

22 Claims, 2 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference	27	Claims	ROMC	Draws D

☐ 7. Document ID: US 6475292 B1

L7: Entry 7 of 19

File: USPT

Nov 5, 2002

Record List Display Page 6 of 9

US-PAT-NO: 6475292

DOCUMENT-IDENTIFIER: US 6475292 B1

TITLE: Photoresist stripping method

DATE-ISSUED: November 5, 2002

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Sahbari; Javad J. Sunnyvale CA

US-CL-CURRENT: 134/3; 430/256

ABSTRACT:

A method for removing photoresist, probing ink and wafer bonding adhesive from a substrate using one or more (C.sub.6 -C.sub.16) olefins, one ore more (C.sub.1 - C.sub.6) alkoxybenzenes, and one ore more organic sulfonic acid compounds is provided.

13 Claims, O Drawing figures Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Constances.	Attachirects	Claims	KOMC	Draw, Dr
								!				

8. Document ID: US 6440647 B1

L7: Entry 8 of 19 File: USPT Aug 27, 2002

US-PAT-NO: 6440647

DOCUMENT-IDENTIFIER: US 6440647 B1

TITLE: Resist stripping process

DATE-ISSUED: August 27, 2002

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Yakobson; Eric Aliso Viejo CA

US-CL-CURRENT: <u>430/329</u>; <u>134/1.3</u>, <u>430/256</u>, <u>430/258</u>, <u>430/331</u>, <u>510/175</u>, <u>510/176</u>

ABSTRACT:

A process for removing patterned negative working resist from the surface of a substrate during manufacture of printed wiring boards is disclosed. The process includes the steps of contacting the patterned resist with a stripping solution containing an alkalinity source as well as a source of ammonium ions. The stripping solution is characterized in that it does not contain volatile organic compounds (VOCs).

20 Claims, 0 Drawing figures

Record List Display Page 7 of 9

Exemplary Claim Number: 1

Full Title Citation Front Review Classification Date Reference Claims KNAC Draw, De

☐ 9. Document ID: US 6368421 B1

L7: Entry 9 of 19

File: USPT

Apr 9, 2002

US-PAT-NO: 6368421

DOCUMENT-IDENTIFIER: US 6368421 B1

TITLE: Composition for stripping photoresist and organic materials from substrate

surfaces

DATE-ISSUED: April 9, 2002

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY Oberlander; Joseph E. Phillipsburg NJ Slezak; Mark S. Sunnyvale CA Khanna; Dinesh N. Flemington NJ Durham; Dana L. Flemington NJ NC Matthews

Spinicelli; Lawrence F.

US-CL-CURRENT: <u>134/40</u>; <u>134/38</u>, <u>134/39</u>, <u>510/175</u>, <u>510/176</u>, <u>510/365</u>

ABSTRACT:

The invention relates to the field of microelectronics, such as integrated circuits, and more particularly to compositions and methods of removing photoresists or other organic materials from the surfaces of substrates used in the fabrication of integrated circuits. In particular the present invention relates to amine-free stripping compositions comprising solvent and surfactant that can effectively remove organic materials without corroding the underlying substrate, and the invention also relates to methods for removing these organic materials with the novel stripping composition.

10 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date Reference	Estable of	 Claims	Колс	Drawe D

	10.	Docum	ent ID): US 6	276372 B1					
L7: E	ntry	10 of	19		•	File: U	SPT	Aug	21,	2001

US-PAT-NO: 6276372

DOCUMENT-IDENTIFIER: US 6276372 B1

TITLE: Process using hydroxylamine-gallic acid composition

DATE-ISSUED: August 21, 2001

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Lee; Wai Mun Fremont CA

US-CL-CURRENT: <u>134/1.3</u>; <u>134/2</u>, <u>134/39</u>, <u>257/E21.255</u>, <u>257/E21.577</u>, <u>257/E21.589</u>, <u>510/175</u>, <u>510/176</u>, <u>510/245</u>, <u>510/254</u>, <u>510/477</u>, <u>510/488</u>, <u>510/499</u>, <u>510/505</u>

ABSTRACT:

A hydroxylamine-gallic compound composition comprises a hydroxylamine compound, at least one alcohol amine compound which is miscible with the hydroxylamine compound and a gallic compound. A process for removing photoresist or other polymeric material or a residue from a substrate, such as an integrated circuit semiconductor wafer including titanium metallurgy, in accordance with this invention comprises contacting the substrate with a hydroxylamine compound, an alcohol amine compound which is miscible with the hydroxylamine compound and a gallic compound for a time and at a temperature sufficient to remove the photoresist, other polymeric material or residue from the substrate. Use of a gallic compound in place of catechol in the composition and process reduces attack on titanium metallurgy by, e.g., about three times.

6 Claims, 34 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 34

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"134/103.2"		313
"134/103.3"		57
"134/104.1"		258
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Search Results - Record(s) 11 through 19 of 19 returned.

☐ 11. Document ID: US 6150282 A

L7: Entry 11 of 19

File: USPT

Nov 21, 2000

US-PAT-NO: 6150282

DOCUMENT-IDENTIFIER: US 6150282 A

TITLE: Selective removal of etching residues

DATE-ISSUED: November 21, 2000

INVENTOR-INFORMATION:

STATE ZIP CODE NAME CITY COUNTRY Rath; David L. Stormville NY Jagannathan; Rangarajan Essex Junction VT McCullough; Kenneth J. Fishkill NY Okorn-Schmidt; Harald F. Putnam Valley NY Madden; Karen P. Poughquag NY Pope; Keith R. Danbury CT

US-CL-CURRENT: 438/745; 134/2, 134/3, 257/E21.228, 257/E21.577, 438/906

ABSTRACT:

Etching residue is selectively removed employing a substantially non-aqueous composition containing a fluoride containing compound and certain organic solvents. Preferred compositions also include an anhydride.

40 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference State St	Claims	KOMO	Draw, Dr
	12	Docume	ent IT). IIS 5	753601 A	imuistir iisimiiros		A. Market and the second		
		12 of		. 003	75500171		File: USPT	May	19,	1998

US-PAT-NO: 5753601

DOCUMENT-IDENTIFIER: US 5753601 A

TITLE: Organic stripping composition

Display Format: REV Change Format

Previous Page Next Page Go to Doc#

Record List Display Page 2 of 7

DATE-ISSUED: May 19, 1998

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Ward; Irl E. Bethlehem PA Michelotti; Francis W. Easton PA

US-CL-CURRENT: 510/176; 134/2, 134/38, 134/40, 510/401

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

1 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference		•	Claims	KWAC	Draw
										_		

☐ 13. Document ID: US 5707947 A

L7: Entry 13 of 19 . File: USPT Jan 13, 1998

US-PAT-NO: 5707947

DOCUMENT-IDENTIFIER: US 5707947 A

TITLE: Organic stripping composition

DATE-ISSUED: January 13, 1998

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Ward; Irl E. Bethlehem PA Michelotti; Francis W. Easton · PA

US-CL-CURRENT: 510/176; 134/2, 134/38, 134/40, 510/175, 510/255, 510/401, 510/402, 510/405, 510/499, 510/505

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

1 Claims, 0 Drawing figures Exemplary Claim Number: 1



14. Document ID: US 5648324 A

L7: Entry 14 of 19

File: USPT

Jul 15, 1997

US-PAT-NO: 5648324

DOCUMENT-IDENTIFIER: US 5648324 A

TITLE: Photoresist stripping composition

DATE-ISSUED: July 15, 1997

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Honda; Kenji Barrington RI Perry; Donald F. North Providence RI Maw; Taishih Cumberland RI

US-CL-CURRENT: 510/176; 134/38, 252/394, 510/255, 510/500

ABSTRACT:

A photoresist stripping composition containing:

- (a) 20-70% by weight of an organic polar solvent having a dipole moment of more than 3.5;
- (b) 70-20% by weight of alkanolamine compounds; and
- (c) 0.1-10% by weight of 2,2'[[methyl-1H-benzothiazol-1-yl)methyl]imino]bisethanol.

4 Claims, 0 Drawing figures Exemplary Claim Number: 1

ins Rovio Clave	graduis Claims	多·公司第二十二	Reference	Date	Classification	Review	Front	Citation	Title	Full

☐ 15. Document ID: US 5556482 A

L7: Entry 15 of 19

File: USPT

Sep 17, 1996

US-PAT-NO: 5556482

DOCUMENT-IDENTIFIER: US 5556482 A

TITLE: Method of stripping photoresist with composition containing inhibitor

DATE-ISSUED: September 17, 1996

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Ward; Irl E. Bethlehem PA Michelotti; Francis W. Easton PA

Record List Display Page 4 of 7

US-CL-CURRENT: <u>134/38</u>; <u>134/2</u>, <u>134/40</u>, <u>510/176</u>, <u>510/401</u>, <u>510/402</u>

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

1 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full Title Citation Front Review Classification Date Reference Claims KWC Draw De Claims Later C

US-PAT-NO: 5496491

DOCUMENT-IDENTIFIER: US 5496491 A

TITLE: Organic stripping composition

DATE-ISSUED: March 5, 1996

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Ward; Irl E. Bethlehem PA Michelotti; Francis W. Easton PA

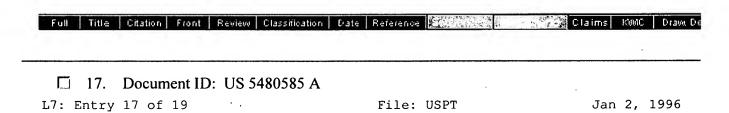
 $\text{US-CL-CURRENT: } \underline{510}/\underline{176}; \ \underline{134}/\underline{38}, \ \underline{252}/\underline{364}, \ \underline{252}/\underline{393}, \ \underline{252}/\underline{394}, \ \underline{252}/\underline{395}, \ \underline{252}/\underline{396},$

<u>510/202</u>, <u>510/212</u>

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

12 Claims, 0 Drawing figures Exemplary Claim Number: 1



US-PAT-NO: 5480585

DOCUMENT-IDENTIFIER: US 5480585 A

TITLE: Stripping liquid compositions

DATE-ISSUED: January 2, 1996

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Shiotsu; Shinichiro Hyogo JP Horiuchi; Yoshiaki Horiuchi JP

US-CL-CURRENT: 510/176; 134/38, 257/E21.255, 430/329, 510/202, 510/212, 510/407,

510/493, 510/505

ABSTRACT:

A photoresist stripping liquid composition comprising an alkanol amine compound, a sulfone compound or sulfoxide compound, and a hydroxy compound. The composition is excellent in its photoresist stripping performance, safety and working efficiency, and does not cause corrosion on a substrate possessing a metal film.

6 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	KMC	Draw. 0

12 18. Document 1D: US 541/8// A

L7: Entry 18 of 19 File: USPT May 23, 1995

US-PAT-NO: 5417877

DOCUMENT-IDENTIFIER: US 5417877 A

TITLE: Organic stripping composition

DATE-ISSUED: May 23, 1995

INVENTOR-INFORMATION:

NAME CITY STATE ZIP CODE COUNTRY

Ward; Irl E. Hatfield PA

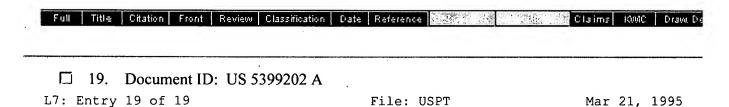
US-CL-CURRENT: $\underline{510}/\underline{176}$; $\underline{134}/\underline{38}$, $\underline{252}/\underline{364}$, $\underline{510}/\underline{202}$, $\underline{510}/\underline{206}$, $\underline{510}/\underline{212}$, $\underline{510}/\underline{255}$,

510/265, 510/500

ABSTRACT:

Organic stripping composition for photoresists comprising organic polar solvents and basic amines which includes an inhibitor which forms a coordination complex with a metal.

12 Claims, O Drawing figures Exemplary Claim Number: 1



US-PAT-NO: 5399202

DOCUMENT-IDENTIFIER: US 5399202 A

TITLE: Resist-peeling liquid and process for peeling a resist using the same

DATE-ISSUED: March 21, 1995

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Kikuchi; Hiroshi	Zushi			JP
Sano; Yasushi	Yokohama	•		JP
Todoroki; Satoru	Yokohama			JP
Oka; Hitoshi	Yokohama			JP
Koshita; Toshiyuki	Mobara			JP
Kikuchi; Masato	Mobara			JP
Nakatani; Mitsuo	Mobara			JP
Tsukii; Michio	Mobara			JP

US-CL-CURRENT: <u>134/1</u>; <u>134/38</u>, <u>510/176</u>, <u>510/202</u>, <u>510/212</u>

ABSTRACT:

A resist is peeled without leaving a residue after peeling, by bringing a resist-peeling liquid comprising a primary aliphatic amine of 2-6 carbon atoms into contact with the surface of an etched novolak positive photoresist, and removing the resist-peeling liquid containing the thus peeled resist from the surface of the etched resist. The used resist-peeling liquid can easily be recovered and regenerated.

8 Claims, 10 Drawing figures Exemplary Claim Number: 1 Number of Drawing Sheets: 5

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